

80V PNP SMALL SIGNAL TRANSISTOR IN SOT323

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

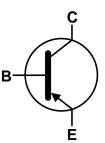
- BV_{CEO} > -80V
- I_C = -500mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMSTA06Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

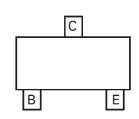
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)







Device Symbol



Pin-out Top View

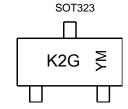
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMSTA56Q-7-F	Automotive	K2G	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K2G = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	2	2016	2017	2018	2019	2020	202	1 20	22 2	2023	2024	2025
Code	С		D	Е	F	G	Н		,	J	K	L	М
Monti	n	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code)	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base Voltage	V _{EBO}	-4	V
Collector Current	I _C	-500	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

Thermal Characteristics and Derating Information

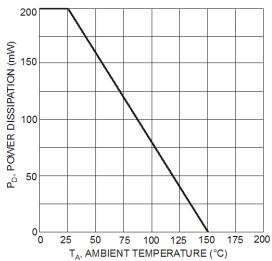


Fig. 1 Max Power Dissipation vs. Ambient Temperature

^{6.} For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{7.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Electrical Characteristics ($@T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)							
Collector-Base Breakdown Voltage	BV _{CBO}	-80	_	V	I _C = -100μA		
Collector-Emitter Breakdown Voltage	BV _{CEO}	-80	_	V	I _C = -1mA		
Emitter-Base Breakdown Voltage	BV _{EBO}	-4	_	V	I _E = -100μA		
Collector Base Cutoff Current	I _{CBO}		-100	nA	$V_{CB} = -80V, T_A = +125^{\circ}C$		
Collector Cutoff Current	I _{CEX}	_	-100	nA	V _{CE} = -80V		
ON CHARACTERISTICS (Note 8)							
DC Current Gain	h	100			$I_C = -10 \text{mA}, V_{CE} = -1.0 \text{V}$		
DC Current Gain	h _{FE}	100	_		$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$		
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.25	V	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$		
Base-Emitter Saturation Voltage	V _{BE(sat)}		-1.2	V	$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$		
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f⊤	50		MHz	$V_{CE} = -1.0V, I_{C} = -100mA,$		
Ourient Gain Bandwidth i roddet	''	30		1711 12	f = 100MHz		

Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

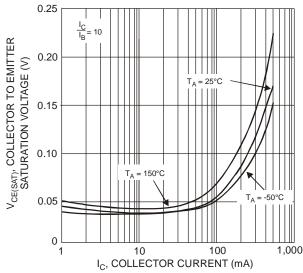


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

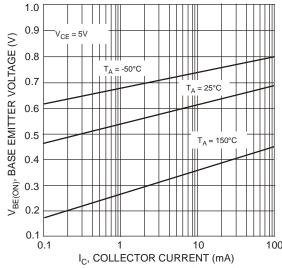


Fig. 4 Base Emitter Voltage vs. Collector Current

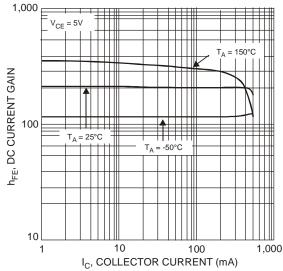


Fig. 3, DC Current Gain vs. Collector Current

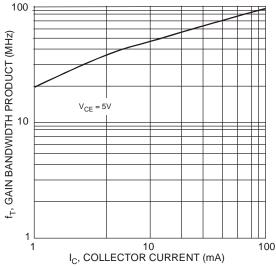
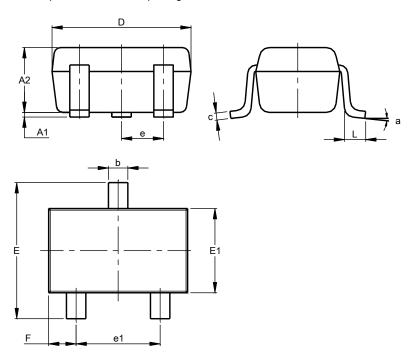


Fig. 5 Gain Bandwidth Product vs. Collector Current



Package Outline Dimensions

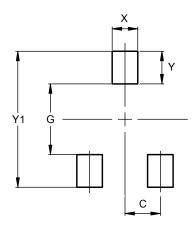
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
E	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value
פווטופווסוטווס	(in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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